PIN diode
RN731V

●Applications

VHF / UHF band variable attenuators and AGC

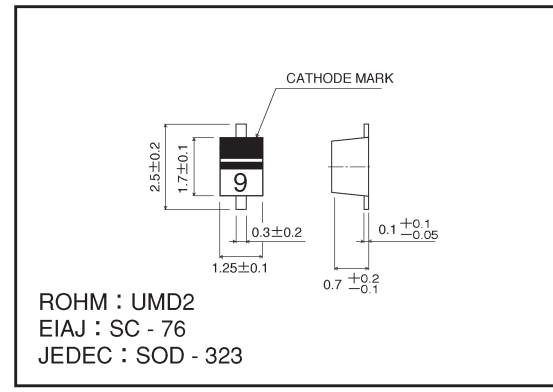
●Features

1) Small surface mounting type. (UMD2)
2) Low high–frequency forward resistance (r_F) / low capacitance (C_T).
3) High reliability.

●Construction

Silicon diffusion junction

●External dimensions (Units: mm)



ROHM：UMD2
EIAJ：SC - 76
JEDEC：SOD - 323

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	50	V
DC forward current	I_F	50	mA
Power dissipation	Pd	100	mW
Junction temperature	Tj	125	℃
Storage temperature	Tstg	−55～+125	℃

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	0.93	1.0	V	I_F=50mA
Reverse current	I_R	—	0.01	100	nA	V_R=50V
Capacitance between terminals	C_T	—	0.23	0.4	pF	V_R=35V, f=1MHz
Forward operating resistance	r_F	—	3.5	7	Ω	I_F=10mA, f=100MHz

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

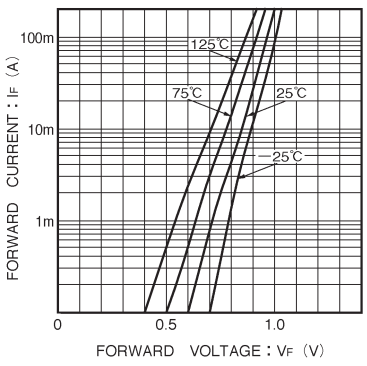


Fig. 1 Forward characteristics

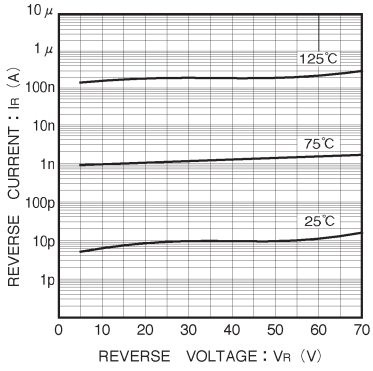


Fig. 2 Reverse characteristics

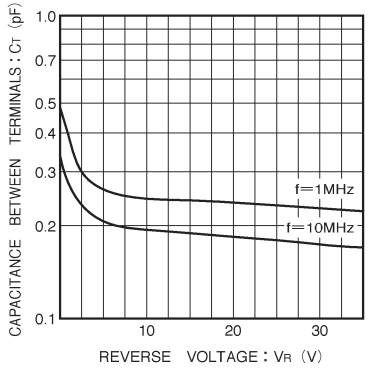


Fig. 3 Capacitance between terminals characteristics (Ⅰ)

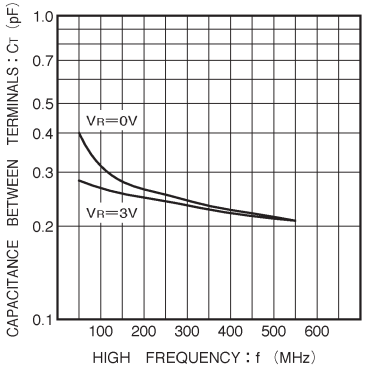


Fig. 4 Capacitance between terminals characteristics (Ⅱ)

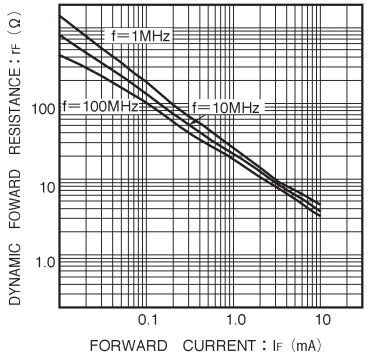


Fig. 5 High frequency characteristics

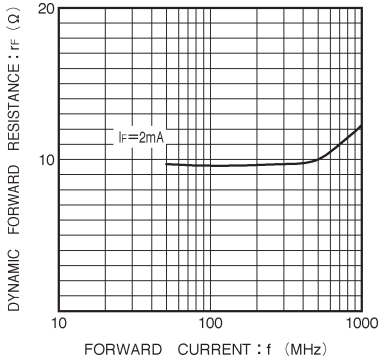


Fig. 6 Forward operating resistance characteristics

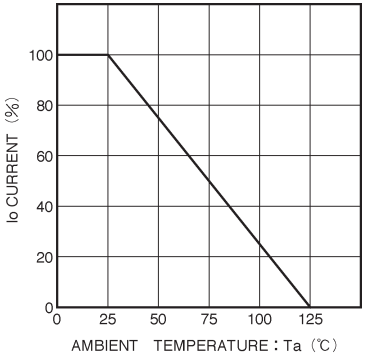


Fig. 7 Derating curve
(mounting on glass epoxy PCBs)